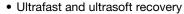


HEXFRED®, **Ultrafast Soft Recovery Diode, 15 A**

FEATURES







· Designed and qualified for industrial level







BENEFITS

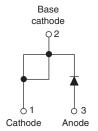
- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA15TB60PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the VS-HFA15TB60PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA15TB60PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.



TO-220AC



PRODUCT SUMMARY					
Package	TO-220AC				
I _{F(AV)}	15 A				
V _R	600 V				
V _F at I _F	1.7 V				
t _{rr} (typ.)	23 ns				
T _J max.	150 °C				
Diode variation	Single die				

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _R		600	V		
Maximum continuous forward current	I _F	T _C = 100 °C	15			
Single pulse forward current	I _{FSM}		150	А		
Maximum repetitive forward current	I _{FRM}		60			
Maximum nauvar dissination	$P_{D} = \frac{T_{C} = 25 \text{ °C}}{T_{C} = 100 \text{ °C}}$	T _C = 25 °C	74	W		
Maximum power dissipation		29] vv			
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C		





ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V_{BR}	Ι _R = 100 μΑ		600	-	-	
		I _F = 15 A		-	1.3	1.7	V
Maximum forward voltage	V_{FM}	I _F = 30 A	See fig. 1	-	1.5	2.0	
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6	
Maximum reverse		V _R = V _R rated	See fig. 2	-	1.0	10	μA
leakage current	I _{RM}	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$	See lig. 2	-	400	1000	μΑ
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	25	50	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body		-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	A/ μ s, $V_R = 30 \text{ V}$	-	19	-	
Reverse recovery time See fig. 5	t _{rr1}	T _J = 25 °C		-	42	60	ns
occ lig. o	t _{rr2}	T _J = 125 °C		-	74	120	
Peak recovery current	I _{RRM1}	T _J = 25 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	4.0	6.0	A nC
See fig. 6	I _{RRM2}	T _J = 125 °C		-	6.5	10	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	84	180	
See fig. 7	Q _{rr2}	T _J = 125 °C		-	241	600	IIC
Peak rate of fall of recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	188	-	A/µs
	dI _{(rec)M} /dt2	T _J = 125 °C		-	160	-	ΑνμS

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	1.7	K/W	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	N/VV	
Weight			-	2.0	-	g	
vveignt			-	0.07	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AC		HFA1	5TB60	•	

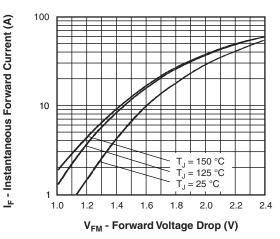


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

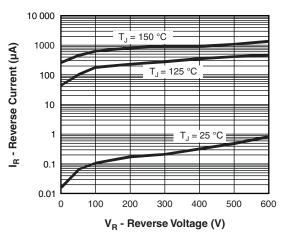


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

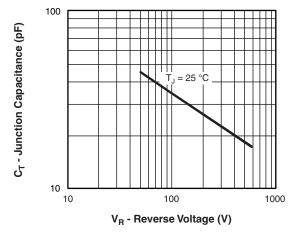


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

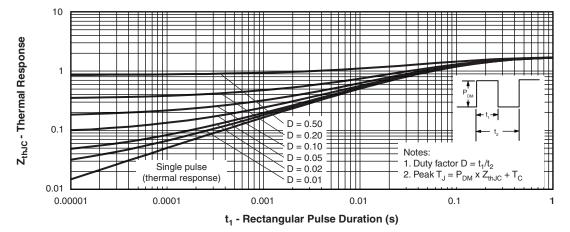


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





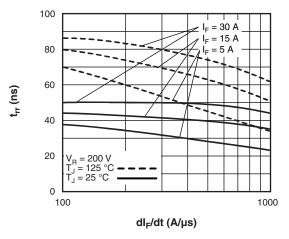


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

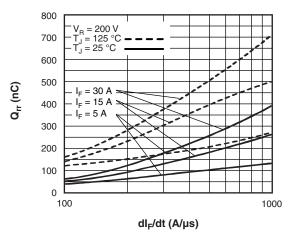


Fig. 7 - Typical Stored Charge vs. dl_F/dt

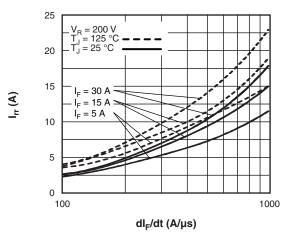


Fig. 6 - Typical Recovery Current vs. dl_F/dt

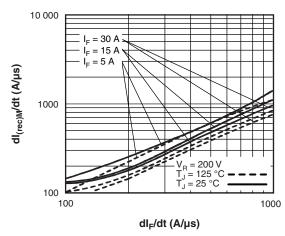


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

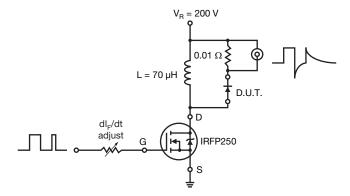
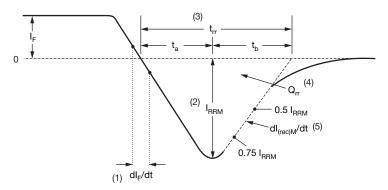


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

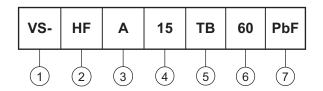
(5) $dI_{(rec)M}/dt$ - peak rate of change of current during $t_{\rm b}$ portion of $t_{\rm rr}$

Fig. 10 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

Electron irradiated

4 - Current rating (15 = 15 A)

5 - Package:

TB = TO-220AC

6 - Voltage rating (60 = 600 V)

7 - PbF = Lead (Pb)-free

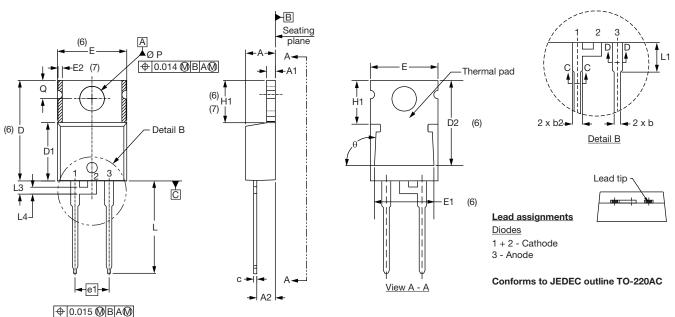
Tube standard pack quantity: 50 pieces

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95221</u>					
Part marking information	www.vishay.com/doc?95224				



TO-220AC

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
Е	10.11	10.51	0.398	0.414	3, 6

CVMPOL	SYMBOL MILLIMETERS INCHES		NOTES		
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
L3	1.78	2.13	0.070	0.084	
L4	0.76	1.27	0.030	0.050	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° to 93°		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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Vishay

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